P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-30	0.018 @ V_{GS} = -10 V	-9.6
	0.030 @ V_{GS} = -4.5 V	-7.5

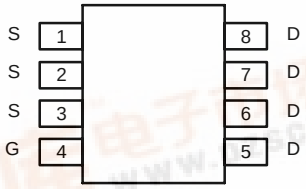
FEATURES

- TrenchFET® Power MOSFET
- Advanced High Cell Density Process

APPLICATIONS

- Load Switches
  - Notebook PCs
  - Desktop PCs

SO-8



Top View

P-Channel MOSFET

Ordering Information: Si4835BDY
Si4835BDY-T1 (with Tape and Reel)

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	-30		V
Gate-Source Voltage		V_{GS}	±25		
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	-9.6	-7.4	A
	T_A = 70°C		-7.7	-5.9	
Pulsed Drain Current		I_{DM}	-50		
continuous Source Current (Diode Conduction)[a]		I_S	-2.1	-1.3	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2.5	1.5	W
	T_A = 70°C		1.6	0.9	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	39	50	°C/W
	Steady State		70	85	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	18	22	

Notes:
a. Surface Mounted on 1” x 1” FR4 Board.

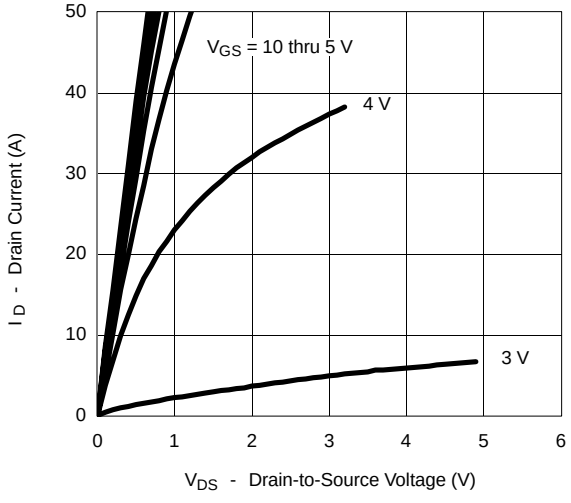
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-1.0		-3.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±25 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -24 V, V_{GS} = 0 V			-1	µA
		V_{DS} = -24 V, V_{GS} = 0 V, T_J = 55°C			-5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≤ -5 V, V_{GS} = -10 V	-50			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = -10 V, I_D = -9.6 A		0.014	0.018	Ω
		V_{GS} = -4.5 V, I_D = -7.5 A		0.023	0.030	
Forward Transconductance[a]	g_{fs}	V_{DS} = -15 V, I_D = -9.6 A		30		S
Diode Forward Voltage[a]	V_{SD}	I_S = -2.1 A, V_{GS} = 0 V		-0.8	-1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = -15 V, V_{GS} = -5 V, I_D = -9.6 A		25	37	nC
Gate-Source Charge	Q_{gs}			6.5		
Gate-Drain Charge	Q_{gd}			12.5		
Gate Resistance	R_g		1.0	2.9	4.9	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -15 V, R_L = 15 Ω I_D ≅ -1 A, V_{GEN} = -10 V, R_G = 6 Ω		15	25	ns
Rise Time	t_r			13	20	
Turn-Off Delay Time	$t_{d(off)}$			60	100	
Fall Time	t_f			45	70	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = -2.1 A, di/dt = 100 A/µs		45	80	

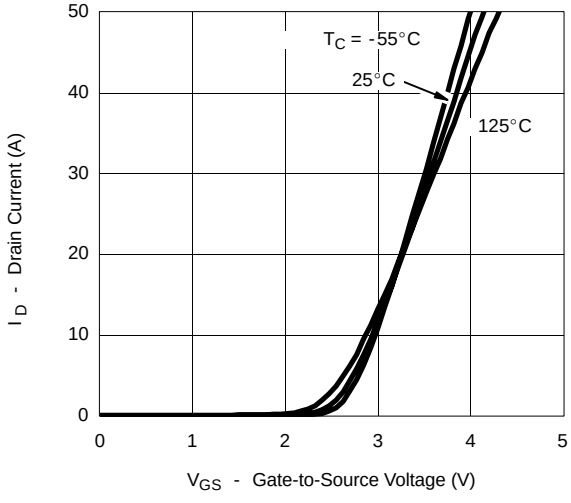
Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Output Characteristics

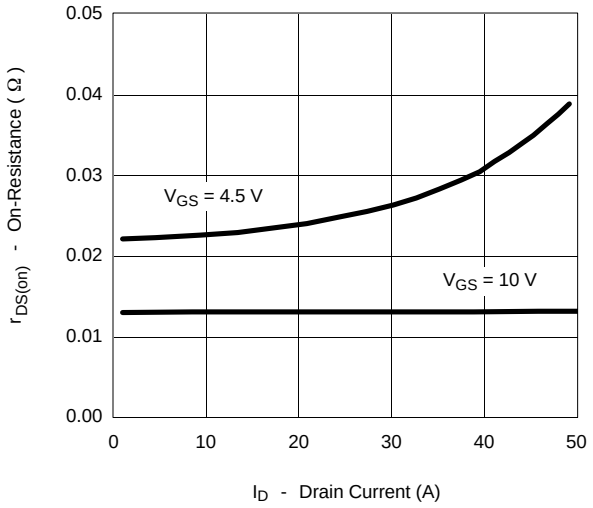


Transfer Characteristics

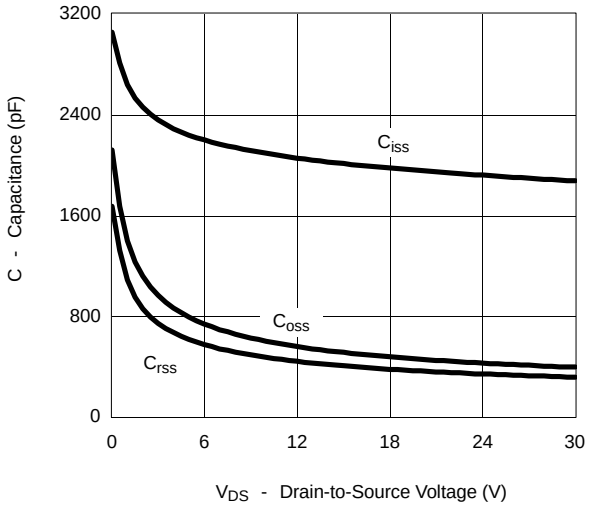


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

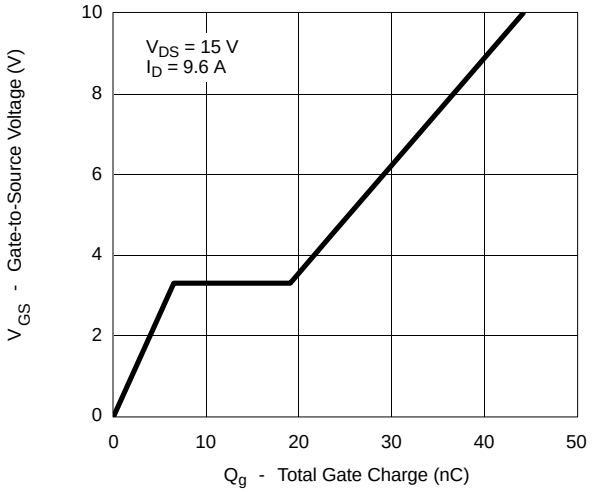
On-Resistance vs. Drain Current



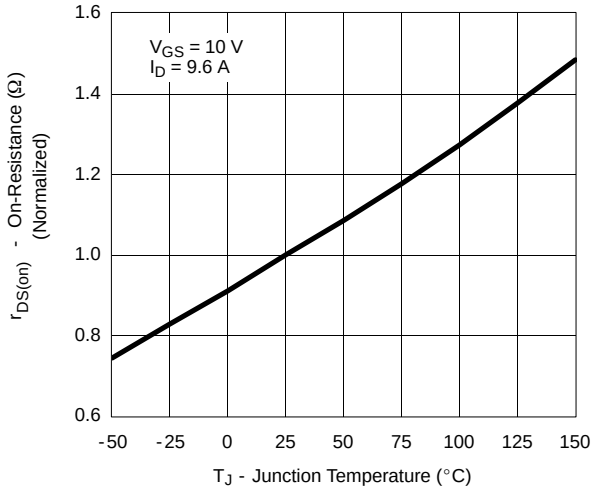
Capacitance



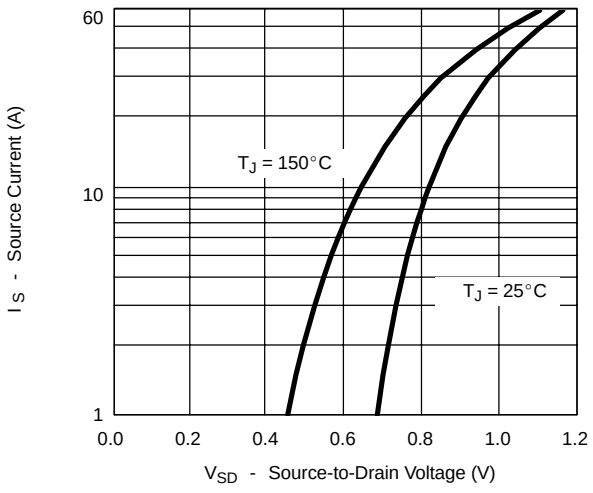
Gate Charge



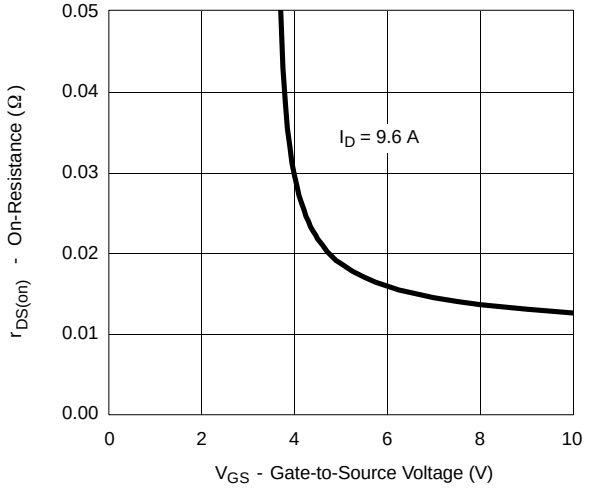
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

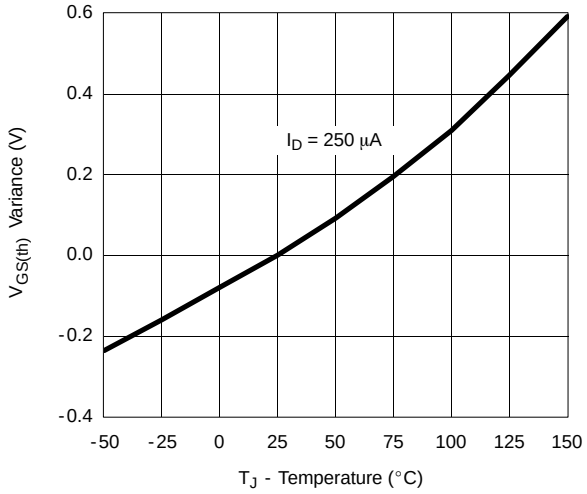


On-Resistance vs. Gate-to-Source Voltage

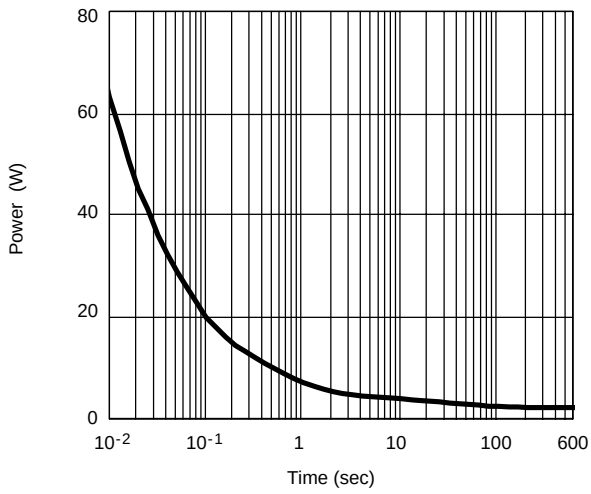


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

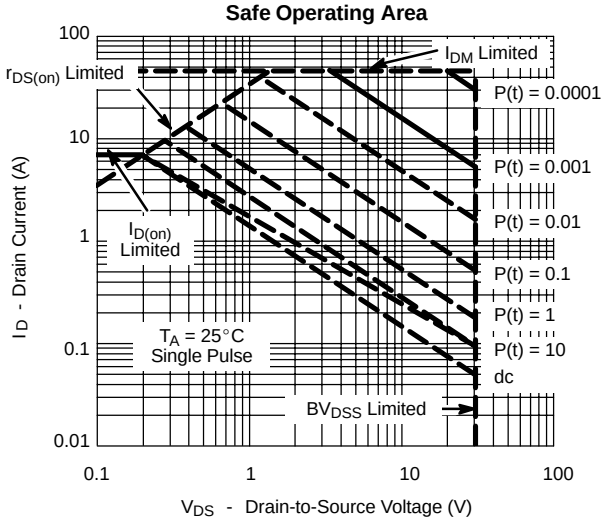
Threshold Voltage



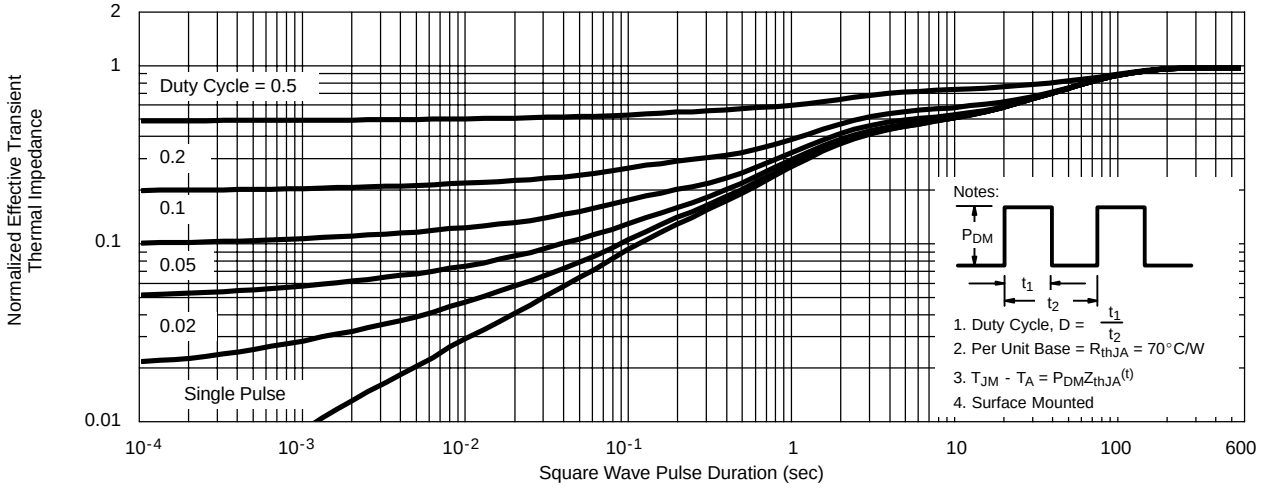
Single Pulse Power, Junction-to-Ambient



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)